

GOA-350

- | | |
|--|---|
| 1. Color | Red |
| 2. Material | AlGaInP / GaP |
| 3. Electrode | N(cathode) side : Au / P(anode) side : Au |
| 4. Electrode pattern | (Fig.) |
| 5. Chip size | 0.325 mm × 0.325 mm × 0.27 mmH (Fig.) |
| 6. Chip structure | Face up: wire bonding |
| 7. Electro-Optical characteristics (Ta = 25°C) | |

Parameters	Symbol	Condition	Characteristics			Unit
			Min.	Typ.	Max.	
Brightness*	Iv	IF = 20mA	300	450	—	mcd
Forward Voltage	VF	IF = 20mA	1.8	2.1	2.3	V
Reverse Current	IR	VR = 5V	—	—	10	μA
Dominant Wavelength	λd	IF = 20mA	615	620	625	nm

*Brightness Measurement at Resonac Photonics.

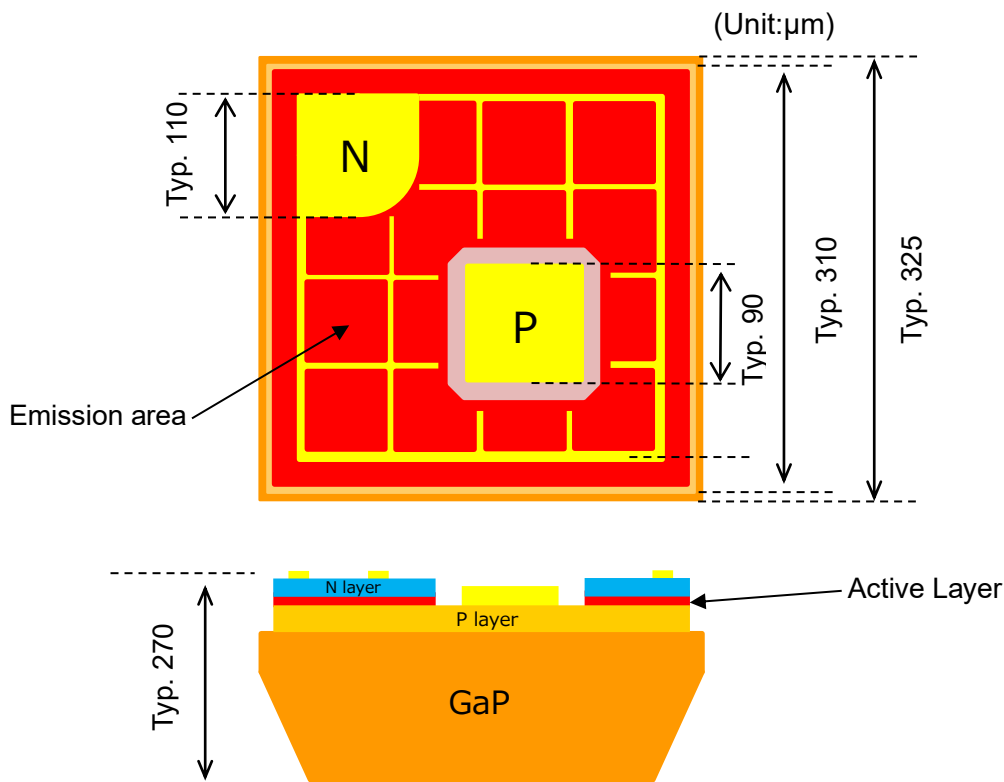


Fig. Chip size & Emission area

The information contained herein is believed to be reliable.
 However, no representations, guaranties or warranties of any kind are made as to accuracy and suitability of the Product for particular applications or the results of its use.
 Resonac Photonics Corporation reserves the right to introduce changes without notice.